

Mikael stling

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

396
papers

7,442
citations

40
h-index

69
g-index

430
ext. papers

8,439
ext. citations

3.2
avg, IF

5.91
L-index

#	Paper	IF	Citations
396	A Silicon Carbide 256 Pixel UV Image Sensor Array Operating at 400 °C. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 116-121	2.3	3
395	Selective Epitaxial Growth of In Situ Doped SiGe on Bulk Ge for p+/n Junction Formation. <i>Electronics (Switzerland)</i> , 2020 , 9, 578	2.6	
394	Process Conditions for Low Interface State Density in Si-passivated Ge Devices with TmSiO Interfacial Layer. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 125009	2	0
393	Manufacture and characterization of graphene membranes with suspended silicon proof masses for MEMS and NEMS applications. <i>Microsystems and Nanoengineering</i> , 2020 , 6, 17	7.7	18
392	Suspended Graphene Membranes with Attached Silicon Proof Masses as Piezoresistive Nanoelectromechanical Systems Accelerometers. <i>Nano Letters</i> , 2019 , 19, 6788-6799	11.5	18
391	Graphene ribbons with suspended masses as transducers in ultra-small nanoelectromechanical accelerometers. <i>Nature Electronics</i> , 2019 , 2, 394-404	28.4	38
390	Towards Silicon Carbide VLSI Circuits for Extreme Environment Applications. <i>Electronics (Switzerland)</i> , 2019 , 8, 496	2.6	12
389	Utilizing the superior etch stop quality of HfO ₂ in the front end of line wafer scale integration of silicon nanowire biosensors. <i>Microelectronic Engineering</i> , 2019 , 212, 13-20	2.5	1
388	Fully inkjet printed ultrathin microsupercapacitors based on graphene electrodes and a nano-graphene oxide electrolyte. <i>Nanoscale</i> , 2019 , 11, 10172-10177	7.7	37
387	Wafer-scale HfO encapsulated silicon nanowire field effect transistor for efficient label-free DNA hybridization detection in dry environment. <i>Nanotechnology</i> , 2019 , 30, 184002	3.4	4
386	Pixel-based biosensor for enhanced control: silicon nanowires monolithically integrated with field-effect transistors in fully depleted silicon on insulator technology. <i>Nanotechnology</i> , 2019 , 30, 225502	3.4	4
385	Editorial Exciting Progress. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 7, 1-1	2.3	
384	Errata for [An Intermediate Frequency Amplifier for High-Temperature Applications][Apr 18 1411-1418]. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 3694-3694	2.9	
383	Suppression of Short-Channel Effects in 4H-SiC Trench MOSFETs. <i>Materials Science Forum</i> , 2019 , 963, 613-616	0.4	2
382	High Temperature High Current Gain IC Compatible 4H-SiC Phototransistor. <i>Materials Science Forum</i> , 2019 , 963, 832-836	0.4	7
381	4H-SiC Trench pMOSFETs for High-Frequency CMOS Inverters. <i>Materials Science Forum</i> , 2019 , 963, 837-840		
380	Wet Transfer of Inkjet Printed Graphene for Microsupercapacitors on Arbitrary Substrates. <i>ACS Applied Energy Materials</i> , 2019 , 2, 158-163	6.1	18

379	A 4H-SiC BJT as a Switch for On-Chip Integrated UV Photodiode. <i>IEEE Electron Device Letters</i> , 2019 , 40, 51-54	4.4	8
378	15 kV-Class Implantation-Free 4H-SiC BJTs With Record High Current Gain. <i>IEEE Electron Device Letters</i> , 2018 , 39, 63-66	4.4	30
377	Scaling and Modeling of High Temperature 4H-SiC p-i-n Photodiodes. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 139-145	2.3	3
376	Germanium on Insulator Fabrication for Monolithic 3-D Integration. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 588-593	2.3	4
375	Editorial Toward Faster Publishing and Shorter Turnaround Time. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 1-1	2.3	2
374	An Intermediate Frequency Amplifier for High-Temperature Applications. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 1411-1418	2.9	5
373	Inkjet-printing of graphene saturable absorbers for ~2 μm bulk and waveguide lasers. <i>Optical Materials Express</i> , 2018 , 8, 2803	2.6	7
372	. <i>IEEE Electron Device Letters</i> , 2018 , 1-1	4.4	14
371	Conductivity Modulated and Implantation-Free 4H-SiC Ultra-High-Voltage PiN Diodes. <i>Materials Science Forum</i> , 2018 , 924, 568-572	0.4	5
370	Humidity and CO2 gas sensing properties of double-layer graphene. <i>Carbon</i> , 2018 , 127, 576-587	10.4	43
369	Investigation of Tm2O3 As a Gate Dielectric for Ge MOS Devices. <i>ECS Transactions</i> , 2018 , 86, 67-73	1	2
368	Monolithic Wafer Scale Integration of Silicon Nanoribbon Sensors with CMOS for Lab-on-Chip Application. <i>Micromachines</i> , 2018 , 9,	3.3	3
367	Influence of Humidity on Contact Resistance in Graphene Devices. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 41738-41746	9.5	9
366	Low Temperature Ni-Al Ohmic Contacts to p-Type 4H-SiC Using Semi-Salicide Processing. <i>Materials Science Forum</i> , 2018 , 924, 389-392	0.4	8
365	4H-SiC pMOSFETs with Al-Doped S/D and NbNi Silicide Ohmic Contacts. <i>Materials Science Forum</i> , 2018 , 924, 423-427	0.4	1
364	Low-Parasitic-Capacitance Self-Aligned 4H-SiC nMOSFETs for Harsh Environment Electronics. <i>Materials Science Forum</i> , 2018 , 924, 971-974	0.4	4
363	Formation of nickel germanides from Ni layers with thickness below 10 nm. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 020602	1.3	4
362	Noninvasive Scanning Raman Spectroscopy and Tomography for Graphene Membrane Characterization. <i>Nano Letters</i> , 2017 , 17, 1504-1511	11.5	14

361	Bipolar integrated circuits in SiC for extreme environment operation. <i>Semiconductor Science and Technology</i> , 2017 , 32, 034002	1.8	21
360	Graphene- and 2D Material-Based Thin-Film Printing 2017 , 161-181		2
359	Smart Power Devices Nanotechnology 2017 , 163-204		2
358	An editorial on the recent advances in high and low temperature electronics. <i>Semiconductor Science and Technology</i> , 2017 , 32, 080201	1.8	2
357	Integration and High-Temperature Characterization of Ferroelectric Vanadium-Doped Bismuth Titanate Thin Films on Silicon Carbide. <i>Journal of Electronic Materials</i> , 2017 , 46, 4478-4484	1.9	3
356	Graphene-based CO ₂ sensing and its cross-sensitivity with humidity. <i>RSC Advances</i> , 2017 , 7, 22329-22339	3.7	49
355	10+ kV Implantation-Free 4H-SiC PIN Diodes. <i>Materials Science Forum</i> , 2017 , 897, 423-426	0.4	1
354	Inkjet printed highly transparent and flexible graphene micro-supercapacitors. <i>Nanoscale</i> , 2017 , 9, 6998-7005	10.1	
353	4H-SiC PIN Diode as High Temperature Multifunction Sensor. <i>Materials Science Forum</i> , 2017 , 897, 630-638	0.4	8
352	4H-SiC Pseudo-CMOS Logic Inverters for Harsh Environment Electronics. <i>Materials Science Forum</i> , 2017 , 897, 669-672	0.4	6
351	Design Optimization of a High Temperature 1.2 kV 4H-SiC Buried Grid JBS Rectifier. <i>Materials Science Forum</i> , 2017 , 897, 455-458	0.4	5
350	. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 882-887	2.9	4
349	Electro-optical effects of high aspect ratio P3HT nanofibers colloid in polymer micro-fluid cells. <i>Optics Letters</i> , 2017 , 42, 2157-2160	3	2
348	Wafer-Scale Statistical Analysis of Graphene FETs Part I: Wafer-Scale Fabrication and Yield Analysis. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3919-3926	2.9	8
347	Wafer-Scale Statistical Analysis of Graphene Field-Effect Transistors Part II: Analysis of Device Properties. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3927-3933	2.9	10
346	500 °C High Current 4H-SiC Lateral BJTs for High-Temperature Integrated Circuits. <i>IEEE Electron Device Letters</i> , 2017 , 38, 1429-1432	4.4	13
345	Scalable Fabrication and Integration of Graphene Microsupercapacitors through Full Inkjet Printing. <i>ACS Nano</i> , 2017 , 11, 8249-8256	16.7	204
344	The impact of atomic layer depositions on high quality Ge/GeO ₂ interfaces fabricated by rapid thermal annealing in O ₂ ambient 2017 ,		1

343	A Wafer-Scale Ni-Salicide Contact Technology on n-Type 4H-SiC. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P197-P200	2	9
342	Direct birefringence and transmission modulation via dynamic alignment of P3HT nanofibers in an advanced opto-fluidic component. <i>Optical Materials Express</i> , 2017 , 7, 52	2.6	3
341	Toward effective passivation of graphene to humidity sensing effects 2016 ,		2
340	Piezoresistive Properties of Suspended Graphene Membranes under Uniaxial and Biaxial Strain in Nanoelectromechanical Pressure Sensors. <i>ACS Nano</i> , 2016 , 10, 9879-9886	16.7	77
339	550 °C 4H-SiC p-i-n Photodiode Array With Two-Layer Metallization. <i>IEEE Electron Device Letters</i> , 2016 , 37, 1594-1596	4.4	19
338	Geometrical Effect Dependency on the On-State Characteristics in 5.6 kV 4H-SiC BJTs. <i>Materials Science Forum</i> , 2016 , 858, 958-961	0.4	3
337	Trilayer Graphene as a Candidate Material for Phase-Change Memory Applications. <i>MRS Advances</i> , 2016 , 1, 1487-1494	0.7	
336	Size Impact of Ordered P3HT Nanofibers on Optical Anisotropy. <i>Macromolecular Chemistry and Physics</i> , 2016 , 217, 1089-1095	2.6	8
335	Sensitivity of the crystal quality of SiGe layers grown at low temperatures by trisilane and germane. <i>Thin Solid Films</i> , 2016 , 613, 38-42	2.2	1
334	Improved designs of Si-based quantum wells and Schottky diodes for IR detection. <i>Thin Solid Films</i> , 2016 , 613, 19-23	2.2	2
333	(Invited) TmSiO as a CMOS-Compatible High-k Dielectric. <i>ECS Transactions</i> , 2016 , 72, 79-89	1	
332	Epitaxial Growth of Ge Strain Relaxed Buffer on Si with Low Threading Dislocation Density. <i>ECS Transactions</i> , 2016 , 75, 615-621	1	6
331	Characterization of 4H-SiC nMOSFETs in Harsh Environments, High-Temperature and High Gamma-Ray Radiation. <i>Materials Science Forum</i> , 2016 , 858, 864-867	0.4	8
330	All-solid-state micro-supercapacitors based on inkjet printed graphene electrodes. <i>Applied Physics Letters</i> , 2016 , 109, 123901	3.4	53
329	Modification of Etched Junction Termination Extension for the High Voltage 4H-SiC Power Devices. <i>Materials Science Forum</i> , 2016 , 858, 978-981	0.4	7
328	Graphene transfer methods for the fabrication of membrane-based NEMS devices. <i>Microelectronic Engineering</i> , 2016 , 159, 108-113	2.5	29
327	Bias-temperature instability on the back gate of single-layer double-gated graphene field-effect transistors. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 04EP03	1.4	5
326	4H-SiC nMOSFETs with As-Doped S/D and NbNi Silicide Ohmic Contacts. <i>Materials Science Forum</i> , 2016 , 858, 573-576	0.4	5

325	Three-Dimensional Integration of Ge and Two-Dimensional Materials for One-Dimensional Devices 2016 , 51-67		
324	(Invited) Emerging Graphene Device Technologies. <i>ECS Transactions</i> , 2016 , 75, 17-35	1	1
323	State of the art power switching devices in SiC and their applications 2016 ,		3
322	. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 4366-4372	2.9	6
321	Dynamic Manipulation of Optical Anisotropy of Suspended Poly-3-hexylthiophene Nanofibers. <i>Advanced Optical Materials</i> , 2016 , 4, 1651-1656	8.1	5
320	Precise percolation thresholds of two-dimensional random systems comprising overlapping ellipses. <i>Physica A: Statistical Mechanics and Its Applications</i> , 2016 , 462, 940-950	3.3	17
319	Conductivity scaling in supercritical percolation of nanoparticles--not a power law. <i>Nanoscale</i> , 2015 , 7, 3424-8	7.7	13
318	Large scale integration of graphene transistors for potential applications in the back end of the line. <i>Solid-State Electronics</i> , 2015 , 108, 61-66	1.7	17
317	Optimizing the optical and electrical properties of graphene ink thin films by laser-annealing. <i>2D Materials</i> , 2015 , 2, 011003	5.9	22
316	Bilayer insulator tunnel barriers for graphene-based vertical hot-electron transistors. <i>Nanoscale</i> , 2015 , 7, 13096-104	7.7	40
315	Conductivity modulated on-axis 4H-SiC 10+ kV PiN diodes 2015 ,		14
314	Threshold voltage control in TmSiO/HfO ₂ high-k/metal gate MOSFETs. <i>Solid-State Electronics</i> , 2015 , 108, 24-29	1.7	4
313	Impact of hot carrier stress on the defect density and mobility in double-gated graphene field-effect transistors 2015 ,		1
312	Residual metallic contamination of transferred chemical vapor deposited graphene. <i>ACS Nano</i> , 2015 , 9, 4776-85	16.7	210
311	Low-Frequency Noise Characterization of Ultra-Low Equivalent-Oxide-Thickness Thulium Silicate Interfacial Layer nMOSFETs. <i>IEEE Electron Device Letters</i> , 2015 , 36, 1355-1358	4.4	1
310	Resistive graphene humidity sensors with rapid and direct electrical readout. <i>Nanoscale</i> , 2015 , 7, 19099-109	10.9	194
309	Hot-Carrier Degradation and Bias-Temperature Instability in Single-Layer Graphene Field-Effect Transistors: Similarities and Differences. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 3876-3881	2.9	20
308	Atomic-layer deposited thulium oxide as a passivation layer on germanium. <i>Journal of Applied Physics</i> , 2015 , 117, 214104	2.5	3

307	Optimal Emitter Cell Geometry in High Power 4H-SiC BJTs. <i>IEEE Electron Device Letters</i> , 2015 , 36, 1069-1072	1.7	9
306	Sputtered Ohmic Cobalt Silicide Contacts to 4H-SiC. <i>Materials Science Forum</i> , 2015 , 821-823, 440-443	0.4	5
305	ECL-Based SiC Logic Circuits for Extreme Temperatures. <i>Materials Science Forum</i> , 2015 , 821-823, 910-913	0.4	12
304	Enhanced Channel Mobility at Sub-nm EOT by Integration of a TmSiO Interfacial Layer in HfO ₂ /TiN High-k/Metal Gate MOSFETs. <i>IEEE Journal of the Electron Devices Society</i> , 2015 , 3, 397-404	2.3	5
303	Going ballistic: Graphene hot electron transistors. <i>Solid State Communications</i> , 2015 , 224, 64-75	1.6	34
302	Investigation of the Breakdown Voltage in High Voltage 4H-SiC BJT with Respect to Oxide and Interface Charges. <i>Materials Science Forum</i> , 2015 , 821-823, 834-837	0.4	7
301	4.5-kV 20-μm ² Implantation-Free 4H-SiC BJT with Trench Structures on the Junction Termination Extension. <i>Materials Science Forum</i> , 2015 , 821-823, 838-841	0.4	2
300	2015 ,		8
299	Characterization of bonding surface and electrical insulation properties of inter layer dielectrics for 3D monolithic integration 2015 ,		1
298	Scalable Fabrication of 2D Semiconducting Crystals for Future Electronics. <i>Electronics (Switzerland)</i> , 2015 , 4, 1033-1061	2.6	19
297	Electric field induced optical anisotropy of P3HT nanofibers in a liquid solution. <i>Optical Materials Express</i> , 2015 , 5, 2642	2.6	10
296	Hot-carrier degradation in single-layer double-gated graphene field-effect transistors 2015 ,		1
295	Influence of Passivation Oxide Thickness and Device Layout on the Current Gain of SiC BJTs. <i>IEEE Electron Device Letters</i> , 2015 , 36, 11-13	4.4	20
294	5.8-kV Implantation-Free 4H-SiC BJT With Multiple-Shallow-Trench Junction Termination Extension. <i>IEEE Electron Device Letters</i> , 2015 , 36, 168-170	4.4	22
293	Integration of TmSiO/HfO ₂ Dielectric Stack in Sub-nm EOT High-k/Metal Gate CMOS Technology. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 934-939	2.9	12
292	Silicon nanowires integrated with CMOS circuits for biosensing application. <i>Solid-State Electronics</i> , 2014 , 98, 26-31	1.7	12
291	New materials for post-Si computing. <i>MRS Bulletin</i> , 2014 , 39, 658-662	3.2	12
290	Bias-temperature instability in single-layer graphene field-effect transistors. <i>Applied Physics Letters</i> , 2014 , 105, 143507	3.4	29

289	Effective workfunction control in TmSiO/HfO ₂ high-k/metal gate stacks 2014 ,		2
288	Fabrication and characterization of silicon nanowires using STL for biosensing applications 2014 ,		2
287	Integrating 3D PIN germanium detectors with high-k ALD fabricated slot waveguides 2014 ,		3
286	Static Nonlinearity in Graphene Field Effect Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 3001-3003	2.9	12
285	Fabrication of strained Ge on insulator via room temperature wafer bonding 2014 ,		1
284	Embedded graphene photodetectors for silicon photonics 2014 ,		2
283	Inkjet Printing of MoS ₂ . <i>Advanced Functional Materials</i> , 2014 , 24, 6524-6531	15.6	167
282	Effects of carbon pre-silicidation implant into Si substrate on NiSi. <i>Microelectronic Engineering</i> , 2014 , 120, 178-181	2.5	13
281	Dependence of the colored frequency noise in spin torque oscillators on current and magnetic field. <i>Applied Physics Letters</i> , 2014 , 104, 092405	3.4	24
280	Biaxial strain in suspended graphene membranes for piezoresistive sensing 2014 ,		4
279	Inkjet printing of 2D layered materials. <i>ChemPhysChem</i> , 2014 , 15, 3427-34	3.2	69
278	Variation of Schottky barrier height induced by dopant segregation monitored by contact resistivity measurements. <i>Microelectronic Engineering</i> , 2014 , 120, 174-177	2.5	4
277	Wafer scale graphene transfer for back end of the line device integration 2014 ,		2
276	. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1199-1206	2.9	69
275	Electrical characterization of thulium silicate interfacial layers for integration in high-k/metal gate CMOS technology. <i>Solid-State Electronics</i> , 2014 , 98, 20-25	1.7	5
274	Lateral p-n-p Transistors and Complementary SiC Bipolar Technology. <i>IEEE Electron Device Letters</i> , 2014 , 35, 428-430	4.4	12
273	Fabrication of Nanowires 2014 , 5-23		
272	Integration of Silicon Nanowires with CMOS 2014 , 65-72		2

271	Fabrication of Relaxed Germanium on Insulator via Room Temperature Wafer Bonding. <i>ECS Transactions</i> , 2014 , 64, 533-541	1	2
270	Chemical vapor deposited graphene: From synthesis to applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 2439-2449	1.6	59
269	SiC Etching and Sacrificial Oxidation Effects on the Performance of 4H-SiC BJTs. <i>Materials Science Forum</i> , 2014 , 778-780, 1005-1008	0.4	17
268	Bias-temperature instability in single-layer graphene field-effect transistors: A reliability challenge 2014 ,		2
267	Graphene-based piezoresistive pressure sensing for uniaxial and biaxial strains 2014 ,		1
266	Recent advances in high-k dielectrics and inter layer engineering 2014 ,		1
265	Characterization of LaxHfyO Gate Dielectrics in 4H-SiC MOS Capacitor. <i>Materials Science Forum</i> , 2014 , 778-780, 549-552	0.4	2
264	Fabrication and Design of 10 kV PiN Diodes Using On-Axis 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 836-840	0.4	6
263	Characterization of Ohmic Ni/Ti/Al and Ni Contacts to 4H-SiC from -40°C to 500°C. <i>Materials Science Forum</i> , 2014 , 778-780, 681-684	0.4	6
262	Interfacial Layer Engineering Using Thulium Silicate/Germanate for High-k/Metal Gate MOSFETs. <i>ECS Transactions</i> , 2014 , 64, 249-260	1	2
261	(Invited) Interface Engineering Routes for a Future CMOS Ge-Based Technology. <i>ECS Transactions</i> , 2014 , 61, 73-88	1	2
260	CVD Growth of GeSnSiC Alloys Using Disilane, Digermene, Tin Tetrachloride and Methylsilane. <i>ECS Transactions</i> , 2014 , 64, 703-710	1	5
259	Thulium Silicate Interfacial Layer for Scalable High-k/Metal Gate Stacks. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 3271-3276	2.9	15
258	Growth of GeSnSiC layers for photonic applications. <i>Surface and Coatings Technology</i> , 2013 , 230, 106-110	4.4	9
257	Silicon nanowires integrated in a fully depleted CMOS process for charge based biosensing 2013 ,		2
256	Mobility enhancement by integration of TmSiO IL in 0.65nm EOT high-k/metal gate MOSFETs 2013 ,		4
255	. <i>IEEE Electron Device Letters</i> , 2013 , 34, 1091-1093	4.4	66
254	Interface engineering of Ge using thulium oxide: Band line-up study. <i>Microelectronic Engineering</i> , 2013 , 109, 204-207	2.5	8

253	Pressure sensors based on suspended graphene membranes. <i>Solid-State Electronics</i> , 2013 , 88, 89-94	1.7	54
252	A graphene-based hot electron transistor. <i>Nano Letters</i> , 2013 , 13, 1435-9	11.5	181
251	A manufacturable process integration approach for graphene devices. <i>Solid-State Electronics</i> , 2013 , 84, 185-190	1.7	20
250	Efficient inkjet printing of graphene. <i>Advanced Materials</i> , 2013 , 25, 3985-92	24	375
249	Electromechanical piezoresistive sensing in suspended graphene membranes. <i>Nano Letters</i> , 2013 , 13, 3237-42	11.5	261
248	Simulation of low Schottky barrier MOSFETs using an improved Multi-subband Monte Carlo model. <i>Solid-State Electronics</i> , 2013 , 79, 172-178	1.7	2
247	Low loss high-k slot waveguides for silicon photonics 2013 ,		2
246	Strain Engineering in GeSnSi Materials. <i>ECS Transactions</i> , 2013 , 50, 527-531	1	14
245	Process Variation Tolerant 4H-SiC Power Devices Utilizing Trench Structures. <i>Materials Science Forum</i> , 2013 , 740-742, 809-812	0.4	1
244	Area-Optimized JTE for 4.5 kV Non Ion-Implanted 4H-SiC BJT. <i>Materials Science Forum</i> , 2013 , 740-742, 974-977	0.4	7
243	High-Temperature Characterization of 4H-SiC Darlington Transistors for Low Voltage Applications. <i>Materials Science Forum</i> , 2013 , 740-742, 966-969	0.4	2
242	A 4H-SiC Bipolar Technology for High-Temperature Integrated Circuits. <i>Journal of Microelectronics and Electronic Packaging</i> , 2013 , 10, 155-162	0.9	10
241	Characterization of SiGe/Si multi-quantum wells for infrared sensing. <i>Applied Physics Letters</i> , 2013 , 103, 251609	3.4	3
240	High-Deposition-Rate Atomic Layer Deposition of Thulium Oxide from TmCp3 and H ₂ O. <i>Journal of the Electrochemical Society</i> , 2013 , 160, D538-D542	3.9	11
239	Percolation thresholds of two-dimensional continuum systems of rectangles. <i>Physical Review E</i> , 2013 , 88, 012101	2.4	37
238	Characterization of thulium silicate interfacial layer for high-k/metal gate MOSFETs 2013 ,		1
237	Power Devices and ICs 2013 , 203-212		2
236	Prevention of Graphene Restacking for Performance Boost of Supercapacitors A Review. <i>Crystals</i> , 2013 , 3, 163-190	2.3	78

235	. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1076-1083	2.9	46
234	. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1585-1591	2.9	3
233	Low-frequency noise in high-k LaLuO ₃ /TiN MOSFETs. <i>Solid-State Electronics</i> , 2012 , 78, 51-55	1.7	8
232	Strain engineering in suspended graphene devices for pressure sensor applications 2012 ,		10
231	An integration approach for graphene double-gate transistors 2012 ,		4
230	2012 ,		7
229	Corrected finite-size scaling in percolation. <i>Physical Review E</i> , 2012 , 86, 040105	2.4	8
228	Impact of oxidation and reduction annealing on the electrical properties of Ge/LaO/ZrO gate stacks. <i>Solid-State Electronics</i> , 2012 , 74, 7-12	1.7	8
227	ALD high-k layer grating couplers for single and double slot on-chip SOI photonics. <i>Solid-State Electronics</i> , 2012 , 74, 58-63	1.7	5
226	Alternative graphene devices: beyond field effect transistors 2012 ,		2
225	Graphene for More Moore and More Than Moore applications 2012 ,		2
224	High performance infra-red detectors based on Si/SiGe multilayers quantum structure. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2012 , 177, 1563-1566	3.1	4
223	Kinetic Modeling of Low Temperature Epitaxy Growth of SiGe Using Disilane and Digermane. <i>Journal of the Electrochemical Society</i> , 2012 , 159, H478-H481	3.9	4
222	Vertical Graphene Base Transistor. <i>IEEE Electron Device Letters</i> , 2012 , 33, 691-693	4.4	129
221	A simple route towards high-concentration surfactant-free graphene dispersions. <i>Carbon</i> , 2012 , 50, 3113-3116	3.1	42
220	Bipolar Integrated OR-NOR Gate in 4H-SiC. <i>Materials Science Forum</i> , 2012 , 717-720, 1257-1260	0.4	1
219	Double slot high-k waveguide grating couplers for silicon photonics 2012 ,		2
218	Threshold of hierarchical percolating systems. <i>Physical Review E</i> , 2012 , 85, 021109	2.4	17

217	RF Performance Projections of Graphene FETs vs. Silicon MOSFETs. <i>ECS Solid State Letters</i> , 2012 , 1, Q39-Q41	18
216	High Current-Gain Implantation-Free 4H-SiC Monolithic Darlington Transistor. <i>IEEE Electron Device Letters</i> , 2011 , 32, 188-190	4.4 4
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6	Stoichiometry determination of reactively sputtered titanium-silicide. <i>Vacuum</i> , 1982 , 32, 665-667	3.7	5
5	Avalanche injection in high voltage Si P-i-N diodes measurements and device simulations		4
4	Extraction of the intrinsic base region sheet resistance in bipolar transistors		4
3	A procedure for characterizing the BJT base resistance and Early voltages utilizing a dual base transistor test structure		2
2	A new procedure for extraction of series resistances for bipolar transistors from DC measurements		5

1	Simulations and measurements of emitter properties in 5 kV Si PIN diodes
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